



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

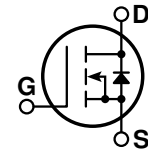
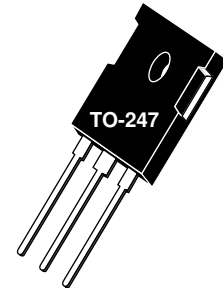
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



POWER MOS V®

Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



- **Faster Switching**
- **100% Avalanche Tested**
- **Lower Leakage**
- **Popular TO-247 Package**

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT4012BVR	UNIT
V_{DSS}	Drain-Source Voltage	400	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	37	Amps
I_{DM}	Pulsed Drain Current ^①	148	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	370	Watts
	Linear Derating Factor	2.96	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	37	Amps
E_{AR}	Repetitive Avalanche Energy ^①	30	mJ
E_{AS}	Single Pulse Avalanche Energy ^④	1300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$)	400			Volts
$I_{D(on)}$	On State Drain Current ^② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10\text{V}$)	37			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10\text{V}, 0.5 I_{D[Cont.]}$)			0.12	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0\text{V}$)			25	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0\text{V}, T_C = 125^\circ\text{C}$)			250	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1.0\text{mA}$)	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

USA
405 S.W. Columbia Street

EUROPE
Avenue J.F. Kennedy Bât B4 Parc Cadéra Nord

APT Website - <http://www.advancedpower.com>

Bend, Oregon 97702-1035

F-33700 Merignac - France

Phone: (541) 382-8028

Phone: (33) 5 57 92 15 15

FAX: (541) 388-0364

FAX: (33) 5 56 47 97 61

DYNAMIC CHARACTERISTICS

APT4012BVR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		4500	5400	pF
C_{oss}	Output Capacitance			690	970	
C_{rss}	Reverse Transfer Capacitance			290	435	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]} @ 25^\circ C$		195	290	nC
Q_{gs}	Gate-Source Charge			25	37	
Q_{gd}	Gate-Drain ("Miller") Charge			90	135	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]} @ 25^\circ C$ $R_G = 1.6\Omega$		14	28	ns
t_r	Rise Time			17	34	
$t_{d(off)}$	Turn-off Delay Time			55	95	
t_f	Fall Time			12	24	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			37	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			148	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_{D[Cont.]}$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_{D[Cont.]}$; $di_S/dt = 100A/\mu s$)		450		ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_{D[Cont.]}$; $di_S/dt = 100A/\mu s$)		7.4		μC

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.34	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

③ See MIL-STD-750 Method 3471

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

④ Starting $T_j = +25^\circ C$, $L = 1.90mH$, $R_G = 25\Omega$, Peak $I_L = 37A$

APT Reserves the right to change, without notice, the specifications and information contained herein.

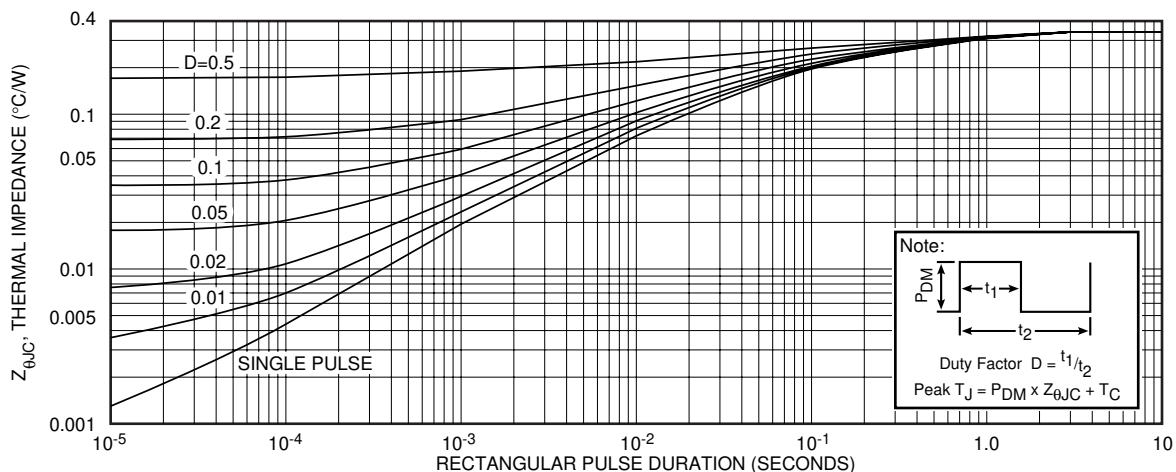


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

APT4012BVR

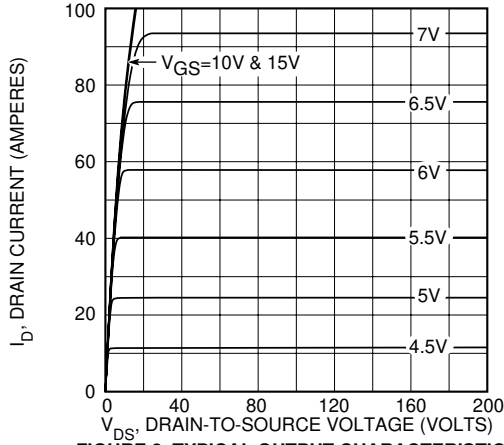


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

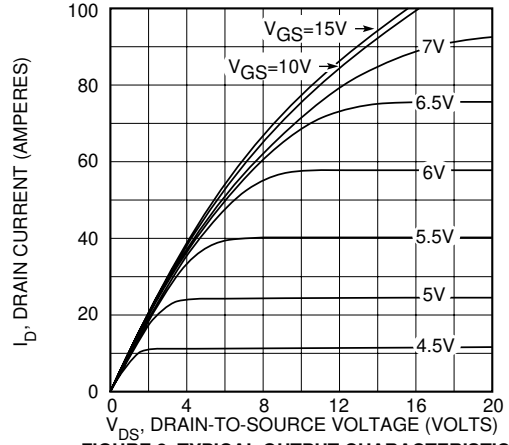


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

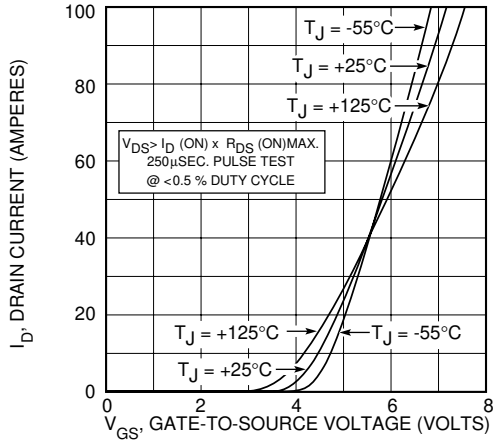


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

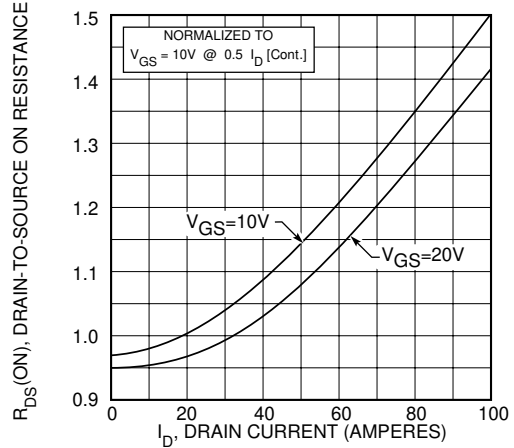


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

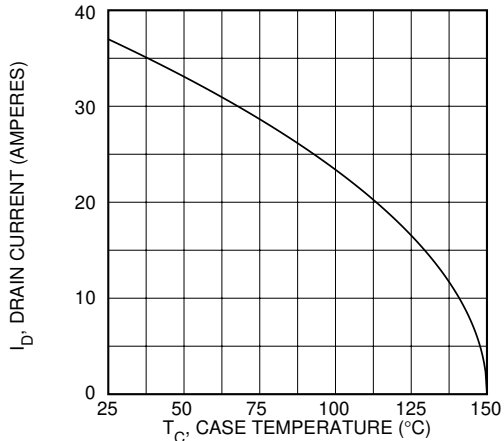


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

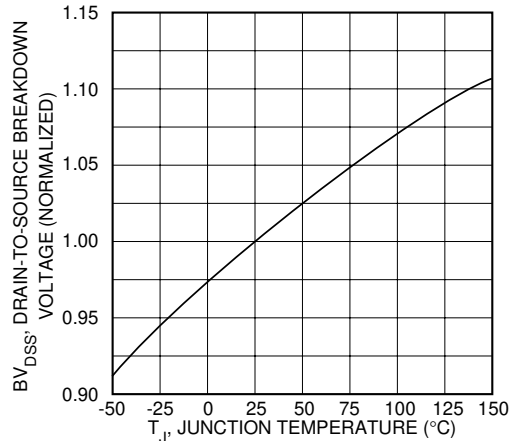


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

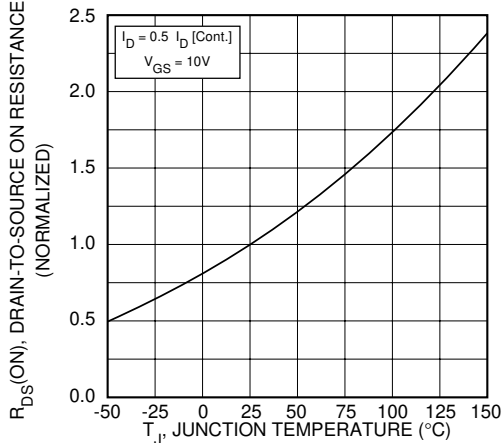


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

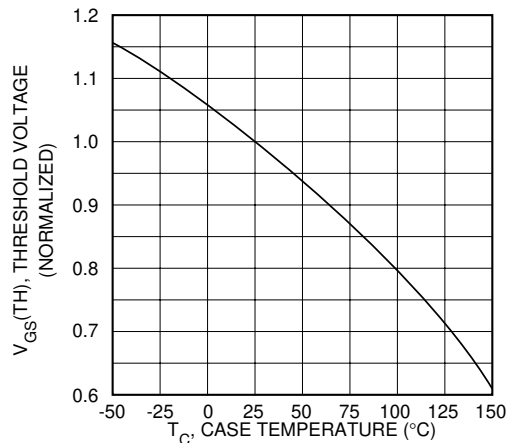


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

APT4012BVR

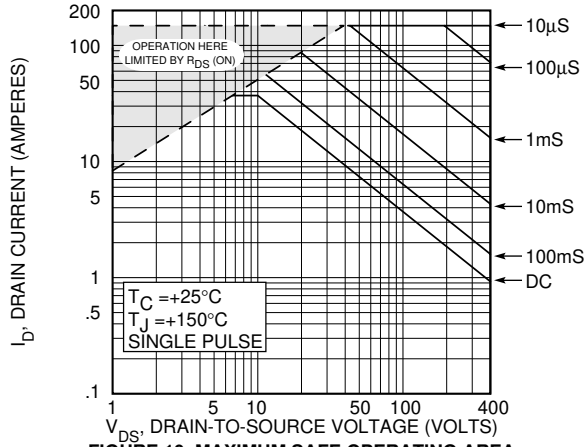


FIGURE 10, MAXIMUM SAFE OPERATING AREA

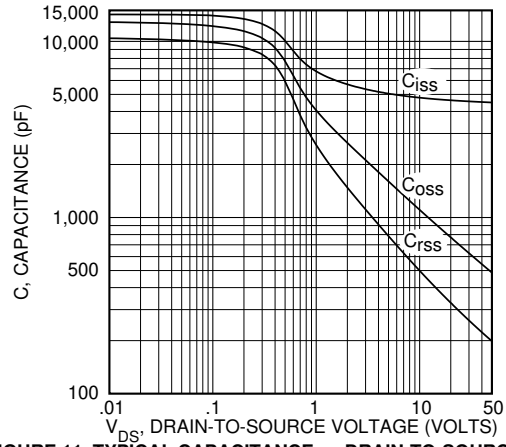


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

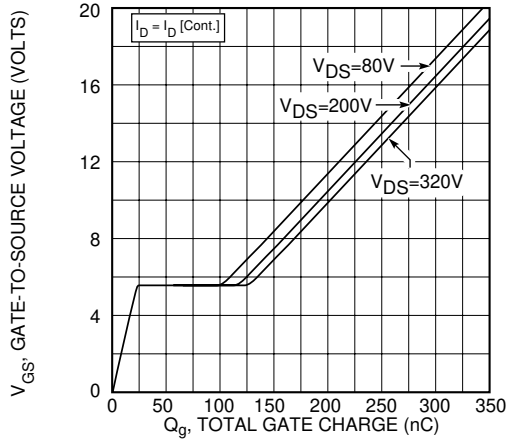


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

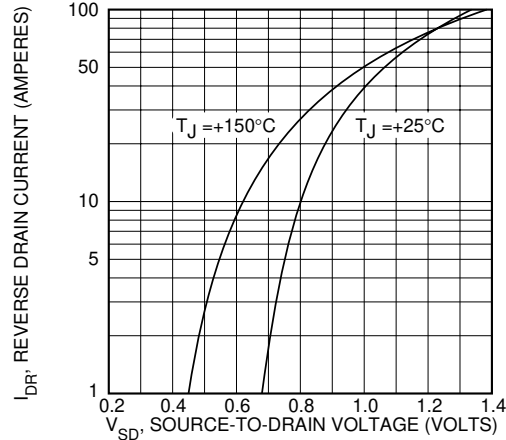
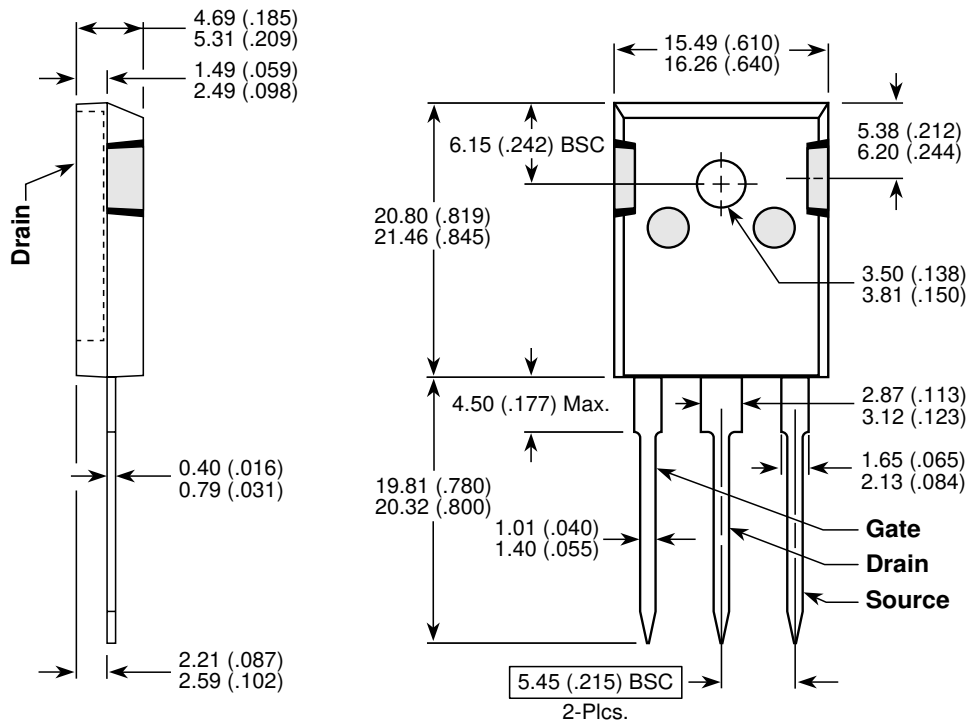


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247 Package Outline



Dimensions in Millimeters and (Inches)